

Absolute maximum ratings

(Ta=25°C)

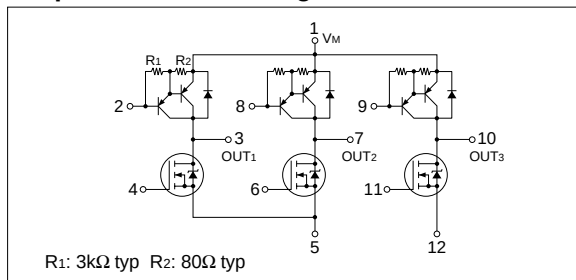
Symbol	Ratings	Unit
V_M	60	V
I_O	± 6 (PW ≤ 100 ms)	A
I_{OP}	± 10 (PW ≤ 1 ms)	A
V_{GS}	± 10	V
I_B	-0.5	A
P_T	5 (Ta=25°C)	W
	35 (Tc=25°C)	
θ_{j-a}	25	°C/W
θ_{j-c}	3.57	°C/W
V_{ISO}	1000 (Between fin and lead pin, AC)	Vrms
T_j	150	°C
T_{stg}	-40 to +150	°C

Electrical characteristics (Sink : N channel MOSFET)

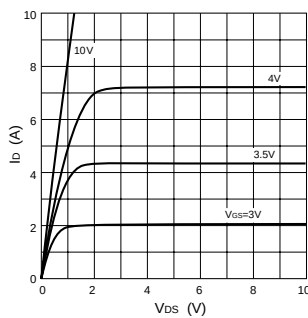
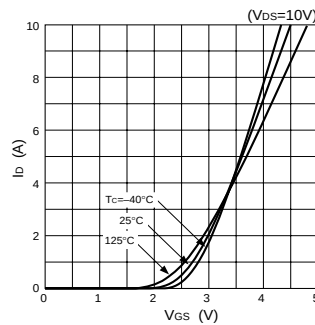
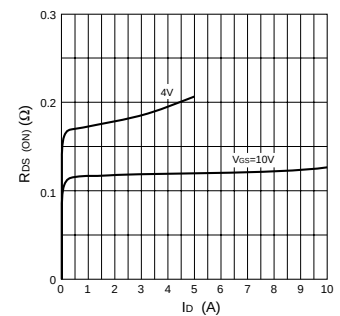
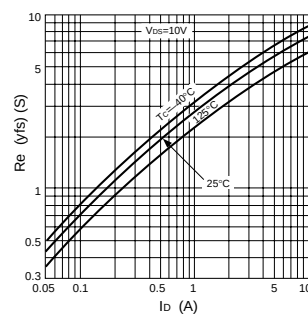
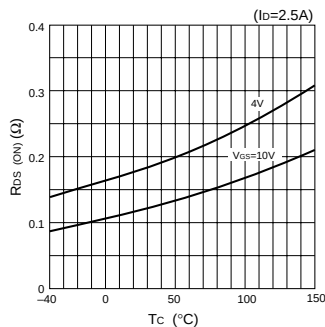
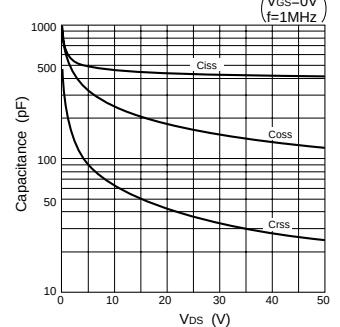
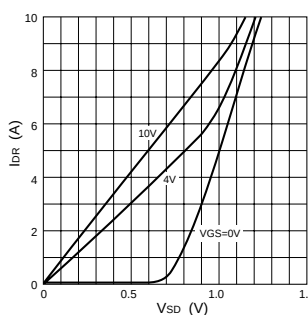
(Ta=25°C)

Symbol	Specification			Unit	Conditions
	min	typ	max		
$V_{(BR)DSS}$	60			V	$I_D=250\mu A$, $V_{GS}=0V$
I_{GSS}			± 500	nA	$V_{GS}=\pm 10V$
I_{DSS}			250	μA	$V_{DS}=60V$, $V_{GS}=0V$
V_{TH}	1.0		2.0	V	$V_{DS}=10V$, $I_D=250\mu A$
$Re(yfs)$	3.1	4.6		S	$V_{DS}=10V$, $I_D=4A$
$R_{DS(ON)}$		0.17	0.22	Ω	$V_{GS}=10V$, $I_D=4A$
		0.25	0.30		$V_{GS}=4V$, $I_D=4A$
C_{iss}		400		pF	$V_{DS}=25V$, $f=1.0MHz$, $V_{GS}=0V$
C_{oss}		160		pF	
t_{on}		80		ns	$I_D=4A$, $V_{DD}=30V$, $V_{GS}=5V$
t_{off}		50		ns	
V_{SD}		1.1	1.5	V	$I_{SD}=4A$, $V_{GS}=0V$
t_{rr}		150		ns	$I_F=\pm 100mA$

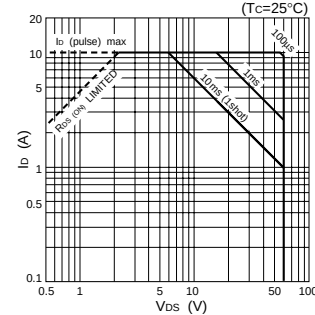
Equivalent circuit diagram



Characteristic curves (N-channel)

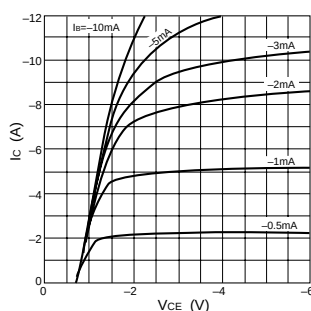
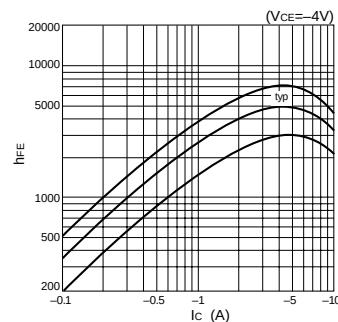
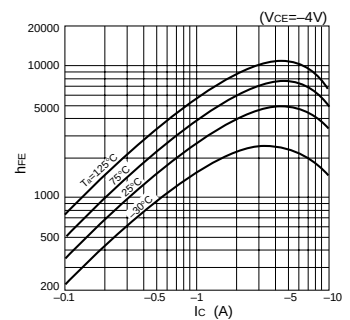
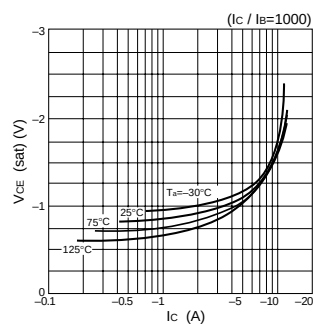
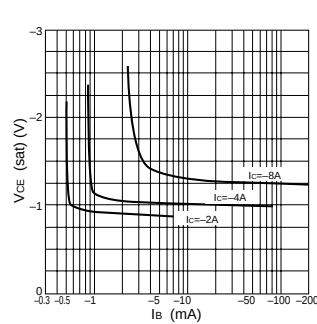
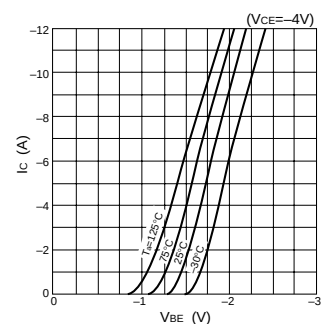
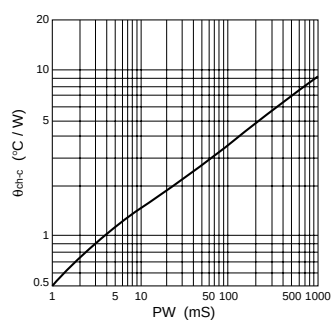
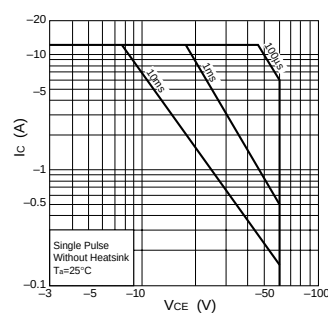
 V_{DS} - I_D Characteristics (Typical) V_{GS} - I_D Temperature Characteristics (Typical) I_{DS} - $R_{DS(ON)}$ Characteristics (Typical) I_D - $Re(yfs)$ Temperature Characteristics (Typical) T_C - $R_{DS(ON)}$ Characteristics (Typical) V_{DS} -Capacitance Characteristics (Typical) V_{SD} - I_{DR} Characteristics (Typical)

Safe Operating Area (SOA)



Electrical characteristics (Source: PNP transistor) (Ta=25°C)

Symbol	Specification			Unit	Conditions
	min	typ	max		
ICBO			-10	μA	$V_{CB} = -60\text{V}$
IEBO	-1		-5	mA	$V_{EB} = -6\text{V}$
VCEO	-60			V	$I_C = -25\text{mA}$
hFE	2000	5000	12000		$V_{CE} = -4\text{V}$, $I_C = -4\text{A}$
VCE(sat)			-1.5	V	$I_C = -4\text{A}$, $I_B = -10\text{mA}$
VBE(sat)			-2.0	V	
VFEC			2.0	V	$I_{FEC} = 4\text{A}$
trr		1.0		μs	$I_F = \pm 0.5\text{A}$
ton		1.0		μs	$V_{CC} = -25\text{V}$, $I_C = -4\text{A}$, $I_{B1} = -I_{B2} = -10\text{mA}$
tstg		1.4		μs	
tf		0.6		μs	
fT		120		MHz	
Cob		150		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$

Characteristic curves (PNP)
IC-VCE Characteristics (Typical)

hFE-IC Characteristics (Typical)

hFE-IC Temperature Characteristics (Typical)

VCE(sat)-IC Temperature Characteristics (Typical)

VCE(sat)-IB Characteristics (Typical)

IC-VBE Temperature Characteristics (Typical)

 θ_{JA} -PW Characteristics

Safe Operating Area (SOA)

PT-Ta Characteristics
